

# Hengyu Xu

## List of Publications by Year in descending order

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3311381

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#	ARTICLE	IF	CITATIONS
1	Influence of phosphorus diffusion on the SiO <sub>2</sub> /4H-SiC (0001) interface during poly gate formation process. <i>Microelectronics Reliability</i> , 2021, 126, 114268.	1.7	1
2	Effect of pulsed UV laser irradiation on 4H-SiC MOS with thermal gate oxide. <i>Journal of Materials Science: Materials in Electronics</i> , 2020, 31, 5838-5842.	2.2	1
3	Wafer Bonding of SiC-AlN at Room Temperature for All-SiC Capacitive Pressure Sensor. <i>Micromachines</i> , 2019, 10, 635.	2.9	4
4	Influence of curvature induced stress on first principle calculation and the reliability of 4H-SiC (0001) thermally grown SiO <sub>2</sub> gate oxide. <i>Microelectronics Reliability</i> , 2019, 100-101, 113317.	1.7	2